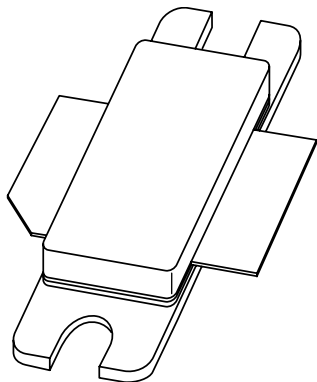


DATA SHEET



BLF2022-70 UHF power LDMOS transistor

Preliminary specification

2000 Sep 21

UHF power LDMOS transistor

BLF2022-70

FEATURES

- High power gain
- Easy power control
- Excellent ruggedness
- Designed for broadband operation (2.0 to 2.2 GHz).
- Internal input and output matching for high gain and efficiency

APPLICATIONS

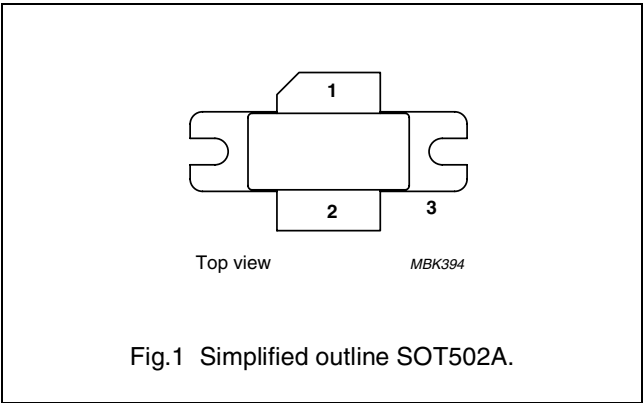
- Common source class-AB operation for PCN and PCS applications in the 2000 to 2200 MHz frequency range.
- W-CDMA, CDMA and multicarrier applications.

DESCRIPTION

Silicon N-channel enhancement mode lateral D-MOS transistor encapsulated in a 2-lead flange SOT502A package with a ceramic cap. The common source is connected to the mounting flange.

PINNING

PIN	DESCRIPTION
1	drain
2	gate
3	source connected to flange



QUICK REFERENCE DATA

RF performance at $T_h = 25\text{ }^{\circ}\text{C}$ in a common source test circuit.

MODE OF OPERATION	f (MHz)	V _{DS} (V)	P _L (W)	G _p (dB)	η_D (%)	d _{im} (dBc)
Two-tone, class-AB	f ₁ = 2200; f ₂ = 2200.1	28	65 (PEP)	>10.5	>30	≤−25

CAUTION
This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling. For further information, refer to Philips specs.: SNW-EQ-608, SNW-FQ-302A and SNW-FQ-302B.

UHF power LDMOS transistor

BLF2022-70

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V_{DS}	drain-source voltage	–	65	V
V_{GS}	gate-source voltage	–	± 15	V
I_D	DC drain current	–	9	A
T_{stg}	storage temperature	–65	+150	°C
T_j	junction temperature	–	200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\,j-h}$	thermal resistance from junction to heatsink	$T_h = 25\text{ °C}$, $P_{tot} = 152\text{ W}$, note 1	1.15	K/W

Note

1. Determined under specified RF operating conditions.

CHARACTERISTICS

 $T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0$; $I_D = 1.4\text{ mA}$	65	–	–	V
V_{GSth}	gate-source threshold voltage	$V_{DS} = 10\text{ V}$; $I_D = 140\text{ mA}$	4.5	–	5.5	V
I_{DSS}	drain-source leakage current	$V_{GS} = 0$; $V_{DS} = 26\text{ V}$	–	–	10	μA
I_{DSX}	on-state drain current	$V_{GS} = V_{GSth} + 9\text{ V}$; $V_{DS} = 10\text{ V}$	18	–	–	A
I_{GSS}	gate leakage current	$V_{GS} = \pm 15\text{ V}$; $V_{DS} = 0$	–	–	22	nA
g_{fs}	forward transconductance	$V_{DS} = 10\text{ V}$; $I_D = 5\text{ A}$	–	4	–	S
R_{DSon}	drain-source on-state resistance	$V_{GS} = V_{GSth} + 9\text{ V}$; $I_D = 5\text{ A}$	–	0.17	–	Ω
C_{rss}	feedback capacitance	$V_{GS} = 0$; $V_{DS} = 26\text{ V}$; $f = 1\text{ MHz}$	–	3.4	–	pF

APPLICATION INFORMATION

RF performance in a common source class-AB circuit. $T_h = 25\text{ °C}$; $R_{th\,j-h} = 1.15\text{ K/W}$; unless otherwise specified.

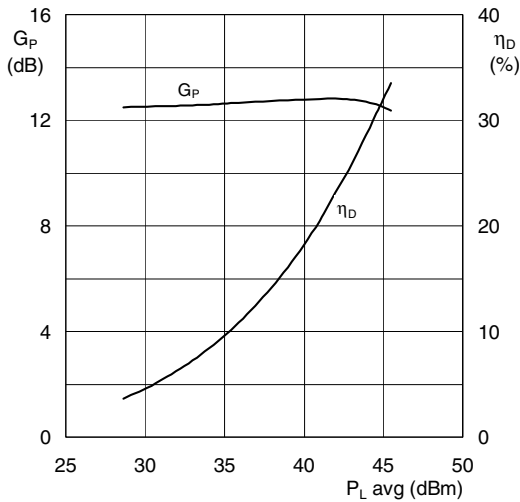
MODE OF OPERATION	f (MHz)	V_{DS} (V)	I_{DQ} (mA)	P_L (W)	G_p (dB)	η_D (%)	d_{im} (dBc)
Two-tone, class-AB	$f_1 = 2200$; $f_2 = 2200.1$	28	500	65 (PEP)	>10.5	>30	≤ -25

Ruggedness in class-AB operation

The BLF2022-70 is capable of withstanding a load mismatch corresponding to $VSWR = 10 : 1$ through all phases under the following conditions: $V_{DS} = 26\text{ V}$; $I_{DQ} = 500\text{ mA}$; $P_L = 65\text{ W (CW)}$; $f = 2200\text{ MHz}$.

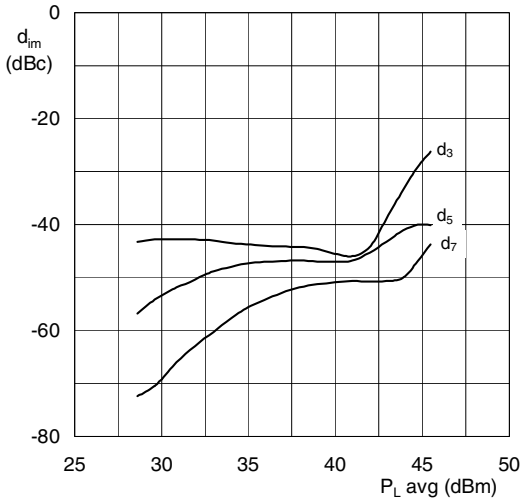
UHF power LDMOS transistor

BLF2022-70



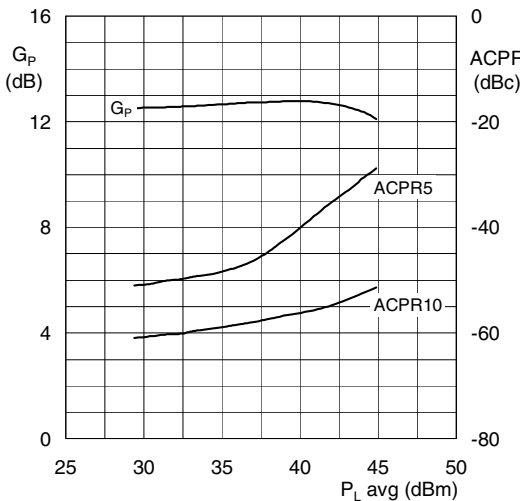
$V_{DS} = 28\text{ V}$; $I_{DQ} = 500\text{ mA}$; $T_h \leq 25\text{ }^\circ\text{C}$;
 $f_1 = 2200\text{ MHz}$; $f_2 = 2200.1\text{ MHz}$.

Fig.2 Power gain and drain efficiency as functions of the average load power; typical values.



$V_{DS} = 28\text{ V}$; $I_{DQ} = 500\text{ mA}$; $T_h \leq 25\text{ }^\circ\text{C}$;

Fig.3 Intermodulation distortion as a function of the average load power; typical values.

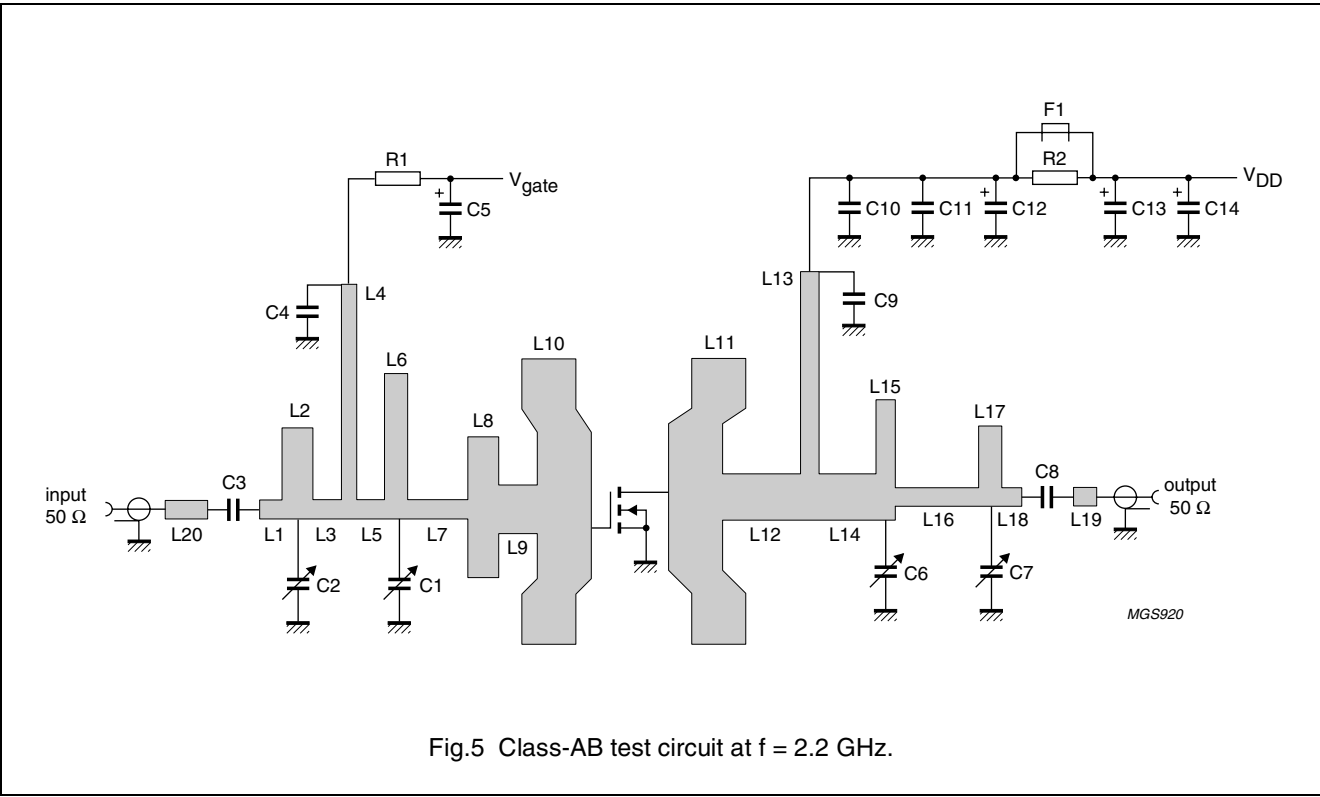


$V_{DS} = 28\text{ V}$; $I_{DQ} = 500\text{ mA}$; $T_h = 25\text{ }^\circ\text{C}$;
 $f_1 = 2200\text{ MHz}$; $f_2 = 2200.1\text{ MHz}$.
Input signal: 3GPP W-CDMA 15DPCH
Peak to average ratio: 10.27 dB (0.0001 %)

Fig.4 Power gain and adjacent channel power ratio as a function of the average load power; typical values.

UHF power LDMOS transistor

BLF2022-70



UHF power LDMOS transistor

BLF2022-70

List of components (See Figs 5 and 6)

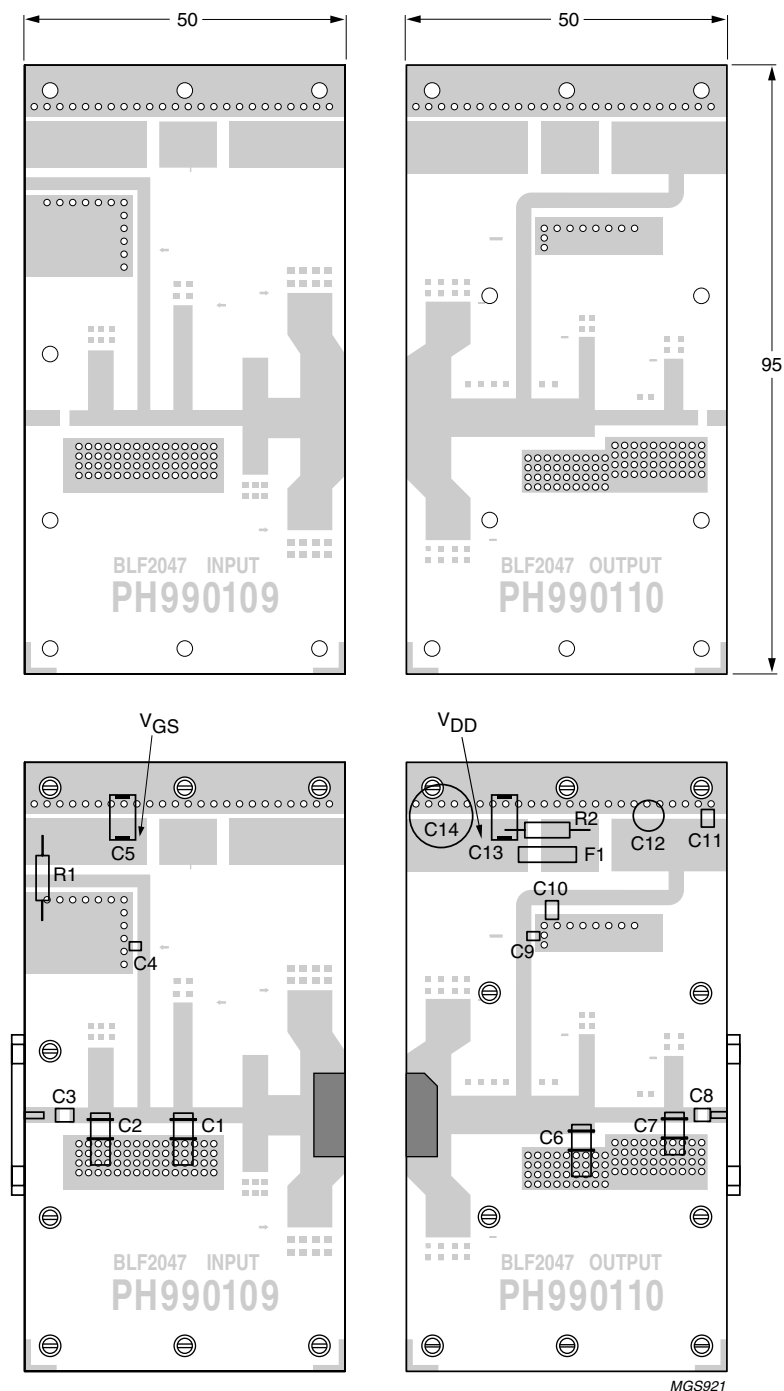
COMPONENT	DESCRIPTION	VALUE	DIMENSIONS	CATALOGUE NO.
C1, C2, C6, C7	Tekelec variable capacitor; type 37281	0.4 to 2.5 pF		
C3, C8	multilayer ceramic chip capacitor; note 1	12 pF		
C4, C9	multilayer ceramic chip capacitor; note 2	12 pF		
C5, C12	electrolytic capacitor	10 μ F; 100 V		2222 037 59109
C10	multilayer ceramic chip capacitor; note 1	1 nF		
C11	multilayer ceramic chip capacitor	100 nF		2222 581 16641
C13	tantal SMD capacitor	4.5 μ F; 50 V		
C14	electrolytic capacitor	100 μ F; 63 V		2222 037 58101
F1	Ferroxcube chip-bead 8DS3/3/8/9-4S2			4330 030 36301
L1	stripline; note 3	50 Ω	2.9 $\times$ 2.4 mm	
L2	stripline; note 3	14.5 Ω	4 $\times$ 11.7 mm	
L3	stripline; note 3	50 Ω	3.7 $\times$ 2.4 mm	
L4	stripline; note 3	6 Ω	2 $\times$ 30.8 mm	
L5	stripline; note 3	50 Ω	3.6 $\times$ 2.4 mm	
L6	stripline; note 3	9.5 Ω	3 $\times$ 18.8 mm	
L7	stripline; note 3	50 Ω	7.8 $\times$ 2.4 mm	
L8	stripline; note 3	9.8 Ω	4 $\times$ 18.3 mm	
L9	stripline; note 3	24.4 Ω	5 $\times$ 6.3 mm	
L10, L11	stripline; note 3	5.1 Ω	7 $\times$ 37 mm	
L12	stripline; note 3	25.4 Ω	10.1 $\times$ 6 mm	
L13	stripline; note 3	5.7 Ω	2.4 $\times$ 32.8 mm	
L14	stripline; note 3	25.4 Ω	7.4 $\times$ 6 mm	
L15	stripline; note 3	11.3 Ω	2.5 $\times$ 15.6 mm	
L16	stripline; note 3	50 Ω	10.8 $\times$ 2.4 mm	
L17	stripline; note 3	16.1 Ω	3 $\times$ 10.4 mm	
L18	stripline; note 3	50 Ω	2.3 $\times$ 2.4 mm	
L19	stripline; note 3	50 Ω	3 $\times$ 2.4 mm	
L20	stripline; note 3	50 Ω	5.5 $\times$ 2.4 mm	
R1, R2	metal film resistor	10 Ω , 0.6 W		2322 156 11009

Notes

1. American Technical Ceramics type 100B or capacitor of same quality.
2. American Technical Ceramics type 100A or capacitor of same quality.
3. The striplines are on a double copper-clad printed-circuit board with Teflon dielectric ($\epsilon_r = 2.2$); thickness 0.79 mm.

UHF power LDMOS transistor

BLF2022-70



Dimensions in mm.

The components are situated on one side of the copper-clad printed-circuit board with Teflon dielectric ($\epsilon_r = 2.2$), thickness 0.79 mm. The other side is unetched and serves as a ground plane.

Fig.6 Component layout for 2.2 GHz class-AB test circuit.

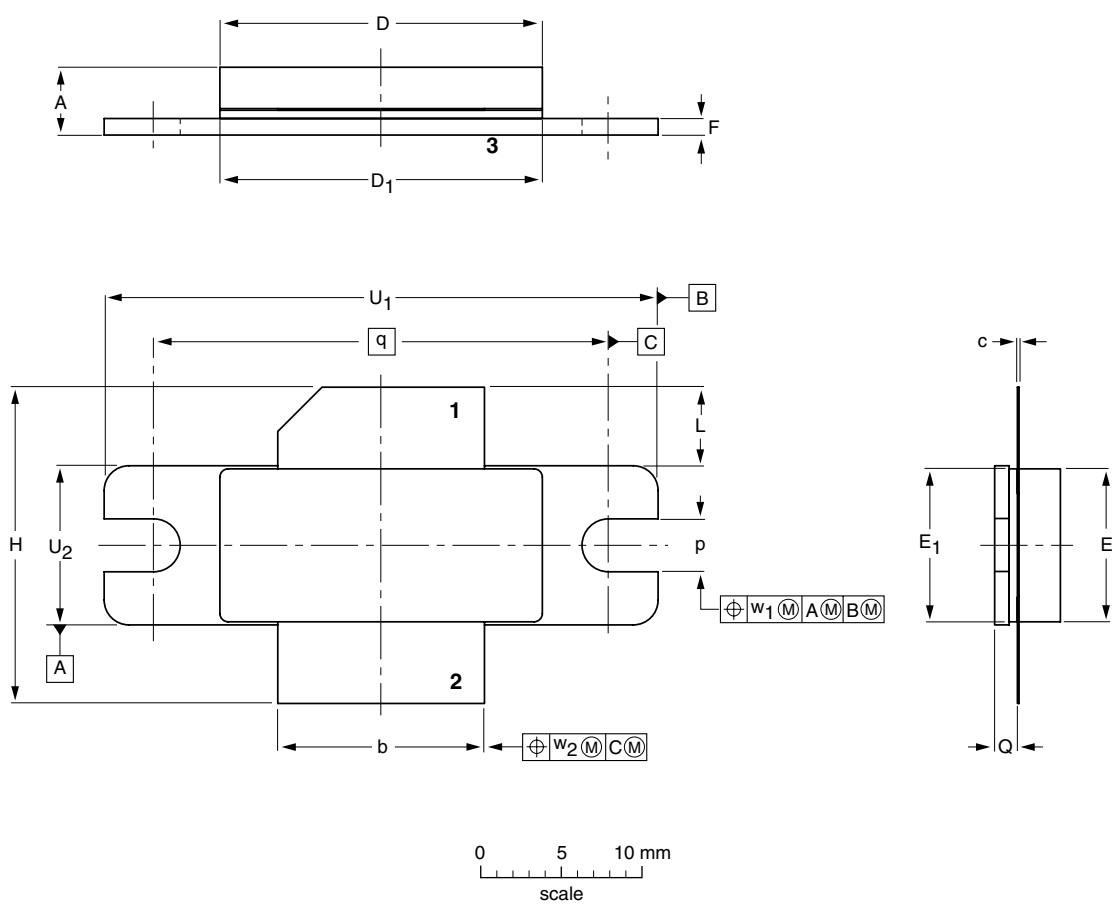
UHF power LDMOS transistor

BLF2022-70

PACKAGE OUTLINE

Flanged LDMOST ceramic package; 2 mounting holes; 2 leads

SOT502A



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D ₁	E	E ₁	F	H	L	p	Q	q	U ₁	U ₂	w ₁	w ₂
mm	4.72 3.99	12.83 12.57	0.15 0.08	20.02 19.61	19.96 19.66	9.50 9.30	9.53 9.25	1.14 0.89	19.94 18.92	5.33 4.32	3.38 3.12	1.70 1.45	27.94	34.16 33.91	9.91 9.65	0.25	0.51
inches	0.186 0.157	0.505 0.495	0.006 0.003	0.788 0.772	0.786 0.774	0.374 0.366	0.375 0.364	0.045 0.035	0.785 0.745	0.210 0.170	0.133 0.123	0.067 0.057	1.100	1.345 1.335	0.390 0.380	0.01	0.02

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT502A						99-10-13 99-12-28

UHF power LDMOS transistor

BLF2022-70

DATA SHEET STATUS

DATA SHEET STATUS	PRODUCT STATUS	DEFINITIONS ⁽¹⁾
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.

Note

1. Please consult the most recently issued data sheet before initiating or completing a design.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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